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1 Improved inversion channel mobility for 4H-SiC MOSFETs following high

temperature anneals in nitric oxide Chung, G.Y.; Tin, C.C.; Williams, J.R.; McDonald, K.; Chanana, R.K.; Weller, R.A.; Pantelides, S.T.; Feldman, L.C.; Holland, O.W.; Das, M.K.; Palmour, J.W.

IEEE Electron Device Letters, Volume: 22 Issue: 4, April 2001 Page(s): 176 -178

Journal or Magazine = JNL Conference = CNF Standard = STD

[Abstract] [PDF Full-Text (56 KB)] JNL

2 Insulator investigation on SiC for improved reliability

Lipkin, L.A.; Palmour, J.W.

Electron Devices, IEEE Transactions on , Volume: 46 Issue: 3, March 1999

Page(s): 525 -532

[Abstract] [PDF Full-Text (176 KB)] JNL

3 Degradation of the characteristics of p/sup +/ poly MOS capacitors with N nitrided gate oxide due to post nitrogen annealing

Mazumder, M.K.; Teramoto, A.; Kobayashi, K.; Sekine, M.; Kawazu, S.; Koyama, H. Integrated Reliability Workshop Final Report, 1997 IEEE International, 1997 Page(s): 142 -143

[Abstract] [PDF Full-Text (192 KB)] CNF

4 Effects of water vap r anneal on MIS devices made of nitrided gate dielectrics

Xiewen Wang; Khare, M.; Ma, T.P.

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5 Water-related degradation of contacts in the multilevel MOS IC with spin-o glasses as interlevel dielectrics

Lifshitz, N.; Lai, W.Y.C.; Smolinsky, G.

IEEE Electron Device Letters , Volume: 10 Issue: 12 , Dec. 1989

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[Abstract] [PDF Full-Text (224 KB)] JNL

6 Advances in processing techniques for silicon micromechanical devices wit smooth surfaces

Guckel, H.; Sniegowski, J.J.; Christenson, T.R. Micro Electro Mechanical Systems, 1989, Proceedings, An Investigation of Micro Structures, Sensors, Actuators, Machines and Robots. IEEE, 1989
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Caliano, G.; Galanello, F.; Caronti, A.; Carotenuto, R.; Pappalardo, M.; Foglietti, V.; Lamberti, N.

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Yota, J.; Janani, M.; Camilletti, L.E.; Kar-Roy, A.; Liu, Q.Z.; Nguyen, C.; Woo, M.D.; Hander, J.; van Cleemput, P.; Chang, W.; Chiou, W.C.; Li, L.J.; Chao, L.C.; Jang, S.M Yu, C.H.; Liang, M.S.

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5 Electrical and reliability characteristics of an ultrathin TaO/sub x/N/sub y gate dielectric prepared by ND/sub 3/ annealing of Ta/sub 2/O/sub 5/

Hyungsuk Jung; Kiju Im; Dooyoung Yang; Hyunsang Hwang IEEE Electron Device Letters , Volume: 21 Issue: 12 , Dec. 2000

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7 Effects of N distribution on charge trapping and TDDB characteristics of N/sub 2/O annealed wet oxide

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Nelms, D.; Ulrich, R.; Schaper, L.; Reeder, S.

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Nung-Pyo Hong; Pil-Gyu Im; Deok-Jung Kim; Kyung-Soon Cho; Don-Chan Cho;

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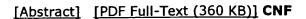
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Micro Electro Mechanical Systems, 1989, Proceedings, An Investigation of Micro

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